AMENDMENTS TO THE SPECIFICATION:

Please amend the title as follows:

--METHOD OF MAKING A REFLECTION TYPE LIQUID CRYSTAL DISPLAY DEVICE ~~AND PROCESS FOR MANUFACTURING THE SAME~~--

Page 4, replace the paragraph beginning on line 7 (paragraph [0011]), bridging page 5, as follows:

--In accordance with a first aspect of the present invention, a process for producing a reflection type liquid crystal display device comprises the steps of (a) depositing a metal layer having a low resistance on an insulating substrate to form [[a]] source/drain ~~wiring~~ electrodes by using a first mask; (b) stacking a silicon layer, gate insulating film and gate electrode layer on said insulating substrate including [[said]] the source/drain ~~wiring~~ electrodes in this order and using a second mask to form a thin film transistor region and a gate ~~wiring by using a second mask~~ electrode; (c) depositing a passivation film on [[said]] the insulating substrate including [[said]] the source/drain ~~wiring~~ electrodes, [[said]] the thin film transistor region and [[said]] the gate ~~wiring~~ electrode, and using a third mask to form an opening ~~for a transistor, in position on said source wiring by using a third mask so that it extends~~ through [[said]] the passivation film; (d) depositing an interlayer film on [[said]] the passivation film ~~to form~~ and

forming a rough surface of [[said]] the interlayer insulating film and using a fourth mask to form an opening ~~for the transistor~~ in a position corresponding to the opening ~~for the transistor~~ in [[said]] the passivation film ~~by using a fourth film~~ so that ~~it extends~~ the openings extend through [[said]] the interlayer insulating film; and (e) depositing a reflective metal over the rough surface of said interlayer insulating film to form, [[by]] with using a fifth mask, a reflection electrode which extends through the respective openings for the transistor in [[said]] the passivation film and [[said]] the interlayer insulating film so that it is electrically connected to [[said]] the source ~~wiring~~ electrode.--

Page 5, replace the paragraph beginning on line 4 (paragraph [0012]), as follows:

--In accordance with a second aspect of the present invention, a process for producing a reflection type liquid crystal display device comprises the steps of (a) depositing a metal layer having a low resistance on an insulating substrate to form [[a]] source/drain ~~wiring~~ electrodes by using a first mask; (b) stacking a silicon layer, gate insulating film and gate electrode layer on [[said]] the insulating substrate including [[said]] the source/drain ~~wiring~~ electrodes in this order and using a second mask to form a thin film transistor region and gate

~~wiring by using a second mask~~ electrode; (c) depositing a passivation film and an interlayer insulating film on [[said]] the insulating substrate including [[said]] the source/drain ~~wiring~~ electrodes, [[said]] the thin film transistor region and [[said]] the gate wiring and using a third mask to form an opening ~~for a transistor~~, in position on [[said]] the source ~~wiring by using a third mask~~ electrode so that [[it]] the opening extends through [[said]] the interlayer insulating film; (d) forming an opening ~~for the transistor~~ extending through [[said]] the passivation film in a position corresponding to the opening ~~for the transistor~~ in [[said]] the interlayer insulating film by using [[said]] the interlayer insulating film as a mask; (e) depositing a reflective metal over the rough surface of said interlayer insulating film to form, by using a fifth mask, a reflection electrode which ~~extend~~ extends through the respective openings ~~for the transistor~~ in [[said]] the passivation film and [[said]] the interlayer insulating film so that [[it]] the reflection electrode is electrically connected to [[said]] the source ~~wiring~~ electrodes.--

Page 15, replace the paragraph beginning on line 10, (paragraph [0023]), bridging page 16, as follows:

PREFERRED EMBODIMENTS OF THE INVENTION

Preferred embodiments of the invention will be now described. In accordance with one preferred embodiment of the

present invention, a process of making a reflection type liquid crystal display device comprises the steps of:

(a) depositing a metal layer having a low resistance on an insulating substrate(10) to form a source/drain ~~wiring~~ electrode(22,23) by using a first mask;

(b) stacking a silicon layer(30), gate insulating film(40) and gate electrode layer(52) in this order on the insulating substrate(10) having the source/drain ~~wiring~~ electrode formed to form a thin film transistor region and a gate ~~wiring~~ electrode by using a second mask;

(c) depositing a passivation film(61) on the insulating substrate including the source/drain ~~wiring~~ electrode, the thin film transistor region and the gate ~~wiring~~ electrode to form an opening(63) for a transistor, in a predetermined position on the source ~~wiring~~ electrode(22) by using a third mask so that the opening penetrates through the passivation film;

(d) depositing an interlayer film(62) on the passivation film(61) to form a rough surface of the interlayer insulating film and to form an opening for the transistor in a position corresponding to the opening for the transistor in the passivation film by using a fourth film so that the opening penetrates through the interlayer insulating film(62); and

(e) depositing a reflective metal layer over the rough surface of the interlayer insulating film(62) to form, by using a

fifth mask, a reflection ~~electrode~~ electrode(71) which penetrates through the respective openings for the transistor in the passivation film(61) and the interlayer insulating film(62) so that reflection ~~electrode~~ electrode(71) is electrically connected to the source ~~wiring~~ electrode(22).

Accordingly, this manufacturing process requires only total 5 PR processes since the formation of the source/drain ~~wiring~~ electrode until the formation of the reflection electrode. The number of the process steps can be remarkably reduced in comparison with those in prior art manufacturing process.

Page 16, replace the paragraph beginning on line 18 (paragraph [0024]), bridging page 17, as follows:

A process for manufacturing a reflection type liquid crystal display device comprises the steps of:

(a) depositing a metal layer having a low resistance on an insulating substrate(10) to form a source/drain ~~wiring~~ electrode(22,23) by using a first mask;

(b) stacking a silicon layer(30), gate insulating film(40) and gate electrode layer(52) in this order on said insulating substrate(10) including said source/drain ~~wiring~~ electrode to form a thin film transistor region and gate ~~wiring~~ electrode by using a second mask;

(c) depositing a passivation film(61) and interlayer insulating film(62) on said insulating substrate including said source/drain ~~wiring~~ electrode, said thin film transistor region and said gate ~~wiring~~ electrode to form, by using a third mask with a half tone exposure method, a rough surface of said interlayer insulating film(62) and an opening for a transistor, in a predetermined position on said source ~~wiring~~ electrode(22) so that the opening penetrates through said interlayer insulating film(62);

(d) forming an opening(63) for the transistor penetrating through said passivation film(61) in a position corresponding to the opening for the transistor in said interlayer insulating film by using said interlayer insulating film(62) as a mask;

(e) depositing a reflective metal over the rough surface of said interlayer insulating film to form, by using a fifth mask, a reflection electrode(71) which extend through the respective openings for the transistor in said passivation film(61) and said interlayer insulating film(62) so that it is electrically connected to said source ~~wiring~~ electrode.

Accordingly, the manufacturing process requires only total of four PR processes since the formation of the source/drain ~~wiring~~ electrode until the formation of the reflection electrode. The number of PR process steps can be further reduced.

Page 18, replace the paragraph beginning on line 23 (paragraph [0028]), bridging page 19, as follows:

--As shown in circuit diagram of Fig. 1, the active matrix substrate 1 comprises a plurality of gate bus lines 51 and a plurality of drain bus lines 21 which intersect to each other on the insulating substrate 10, a plurality of transistors which are disposed at the intersections of the bus lines, and a reflection electrode (not shown). The plurality of gate bus lines 51 and drain bus lines 21 are terminated at the periphery of the insulating substrate 10 and are provided with gate terminals 53 and drain terminals 25, respectively to which drive signals are supplied externally of the substrate. A common potential supply terminal 91 is formed at a corner of the insulating substrate 10. The common potential supply terminal 91 is configured to supply a common potential to a common electrode 92 on an opposite substrate (not shown) which is opposite to the active matrix substrate 1 for ~~sand-witching~~ sandwiching a liquid crystal 81 therebetween. A storage capacitor 3 is formed between each of transistors 2 and the adjacent gate bus line 51 for keeping the potential stored in the pixel constant for a period of one frame.--